

TRANSISTOR (NPN)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

$$P_{CM}: 0.6W (T_{amb}=25^{\circ}C)$$

Collector current

$$I_{CM}: 0.8A$$

Collector-base voltage

$$V_{(BR)CBO}: 35V$$

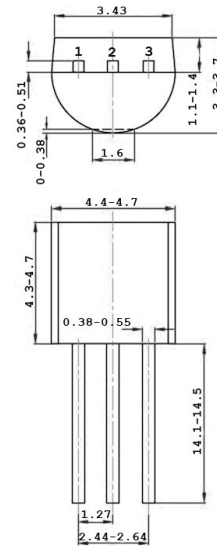
Operating and storage junction temperature range

$$T_{stg}: -55^{\circ}C \text{ to } +150^{\circ}C$$

$$T_J: 150^{\circ}C$$

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=0.1mA, I_E=0$	35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=0.1mA, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=25V, I_B=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=1V, I_C=100mA$	100	320	
Collector-emitter saturation voltage	V_{CEsat}	$I_C=500mA, I_B=20mA$		0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=1V, I_C=10mA$		0.8	V
Transition frequency	f_r	$V_{CE}=5V, I_C=10mA$	100		MHz

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	100-200	160-320